



**JST16F-800C 16A TRIAC**

Rev.A.1.1

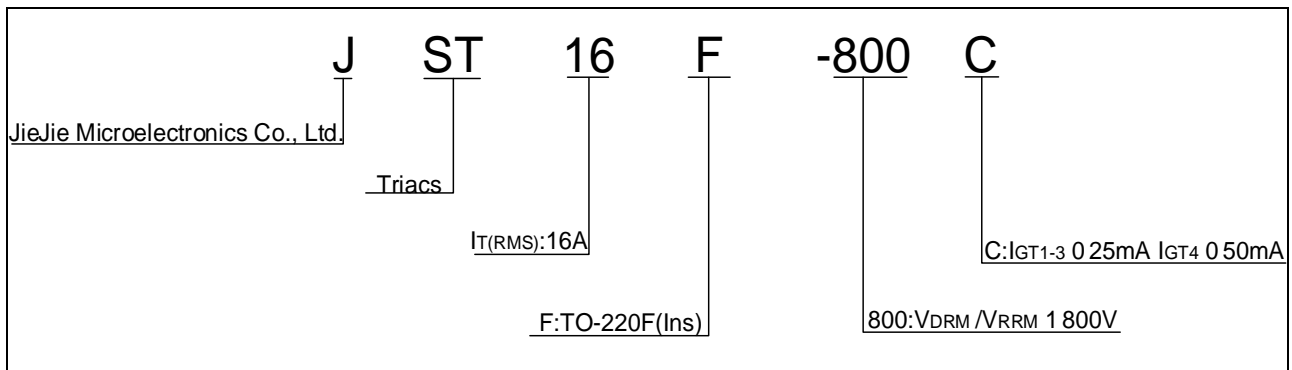
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# JST16F-800C

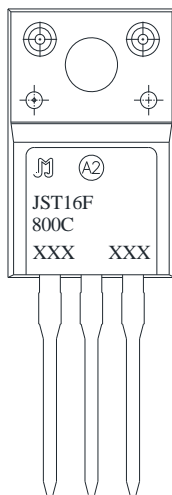
Peak gate power	$P_{GM}$	10	W
Peak pulse voltage ( $T_j=25$ ; non-repetitive,off-state;FIG.7)	$V_{pp}$	3.5	kV

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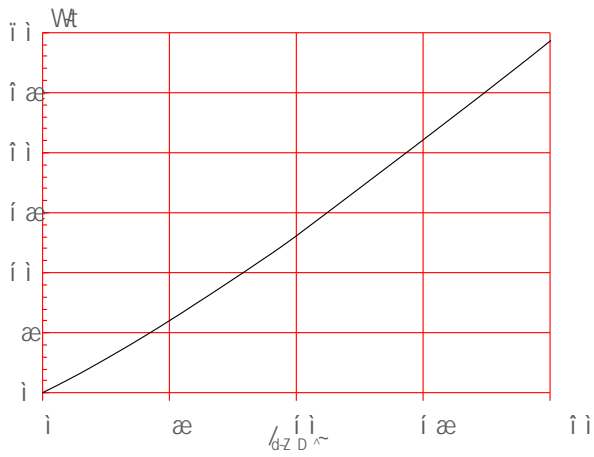
## ORDERING INFORMATION



## MARKING



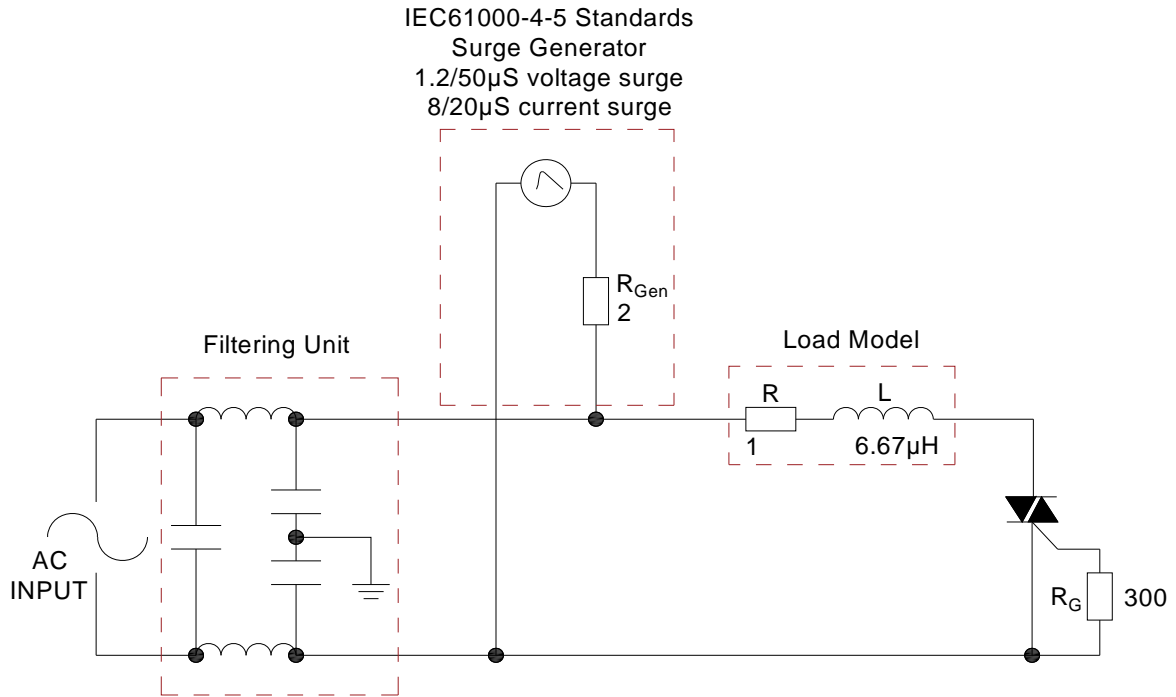
**FIG.1:** Maximum power dissipation versus RMS on-state current



**FIG.2:** RMS on-state current versus case temperature



FIG.7 ÖTest circuit for inductive and resistive loads to IEC-61000-4-5 standards




### LEAD FORMING AND SOLDERING





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